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(71) Applicant: SURFACE TECHNOL SYST LTD

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(54) METHOD FOR ETCHING WORK AND APPARATUS THEREFOR

(57) Abstract:

PROBLEM TO BE SOLVED: To improve the efficiency of an etching stage by continuously supplying gaseous XeF2 and executing etching while the etching is heretofore executed by pulsatively supplying gaseous XeF2.

SOLUTION: An XeF2 supplying section 12 consists of an XeF2 source chamber 16 including a tray and ampoule 17 for an XeF2 crystal 17a, a tank 18 via a valve 19, a flow rate controller 13 supplied with this material by the tank 18 and a valve 20 between the tank 18 and the flow rate controller 13. Pressure sources 21, 22 are provided respectively to maintain the tank 18 and the XeF2 source chamber 16 at the sublimation pressure of the XeF2. This apparatus ensures the stable supply of the XeF2 to an etching chamber.

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